

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

BAS21SLT1G, NSVBAS21SLT1G

Dual Series High Voltage Switching Diode

Features

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: Class 1
 - Machine Model: Class B
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	250	Vdc
Repetitive Peak Reverse Voltage	V _{RRM}	250	Vdc
Peak Forward Current	I _F	225	mAdc
Peak Forward Surge Current	I _{FM(surge)}	625	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

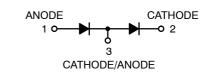
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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SOT-23 CASE 318 STYLE 11

MARKING DIAGRAM



JT = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

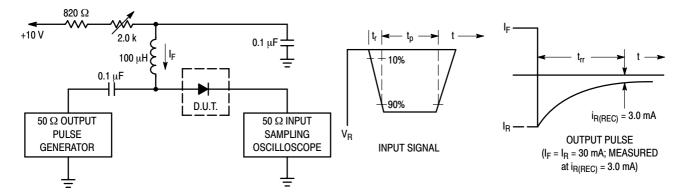
Device	Package	Shipping [†]
BAS21SLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBAS21SLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAS21SLT1G, NSVBAS21SLT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Reverse Voltage Leakage Current (V _R = 200 Vdc) (V _R = 200 Vdc, T _J = 150°C)	I _R	- -	0.1 100	μAdc		
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	250	-	Vdc		
Forward Voltage (I _F = 100 mAdc) (I _F = 200 mAdc)	V _F	- -	1000 1250	mV		
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	-	5.0	pF		
Reverse Recovery Time (I _F = I _R = 30 mAdc, R _L = 100 Ω)	t _{rr}	-	50	ns		



Notes: 1. A 2.0 $k\Omega$ variable resistor adjusted for a Forward Current (IF) of 30 mA.

- 2. Input pulse is adjusted so I_{R(peak)} is equal to 30 mA.
- $3. t_p * t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

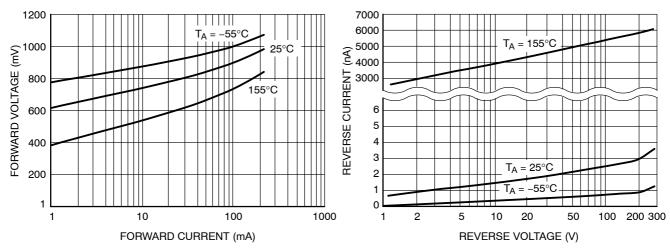


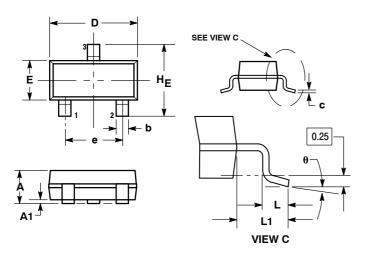
Figure 2. Forward Voltage

Figure 3. Reverse Leakage

BAS21SLT1G, NSVBAS21SLT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



NOTES:

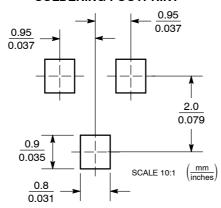
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 11: PIN 1. ANODE CATHODE 2.

CATHODE-ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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